



EV026160662US

Inventor: Zhongze Wang

Title: Silicon-On-Insulator Comprising Integrated Circuitry and Methods of Forming Silicon-On-Insulator Circuitry

Assignee: Micron Technology, Inc.

**INFORMATION DISCLOSURE STATEMENT**

References – See Attached Form PTO-1449

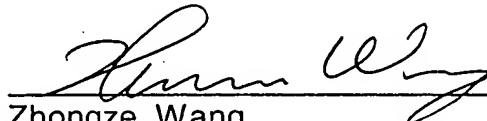
The attached form PTO-1449 is submitted in compliance with 37 CFR § 1.56. Copies of the cited art are included. No admission is made regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated:

1/2/2002


Inventor:

  
Zhongze Wang

Dated:

1-16-02

Attorney:

  
Mark S. Matkin  
Reg. No. 32,268

|  |  |                                      |                       |
|--|--|--------------------------------------|-----------------------|
| Form PTO 414<br><b>U.S. DEPARTMENT OF COMMERCE</b><br><b>PATENT AND TRADEMARK OFFICE</b> |  | ATTY. DOCKET NO.<br>MI22-1797        | SERIAL NO.<br>Unknown |
| <b>LIST OF ART CITED BY APPLICANT</b><br>(Use several sheets if necessary)               |  | APPLICANT<br>Micron Technology, Inc. |                       |
| FILING DATE<br>Filed Herewith  |  | GROUP<br>Unknown                     |                       |

OFFICE  
 DEC 30 2003  
 PATENT & TRADEMARK OFFICE

COPY

| U.S. PATENT DOCUMENTS |                 |      |      |       |          |                            |  |
|-----------------------|-----------------|------|------|-------|----------|----------------------------|--|
| *Examiner Initial     | Document Number | Date | Name | Class | Subclass | Filing Date If Appropriate |  |
|                       | AA              |      |      |       |          |                            |  |
|                       | AB              |      |      |       |          |                            |  |
|                       | AC              |      |      |       |          |                            |  |
|                       | AD              |      |      |       |          |                            |  |
|                       | AE              |      |      |       |          |                            |  |
|                       | AF              |      |      |       |          |                            |  |
|                       | AG              |      |      |       |          |                            |  |
|                       | AH              |      |      |       |          |                            |  |
|                       | AI              |      |      |       |          |                            |  |
|                       | AJ              |      |      |       |          |                            |  |
|                       | AK              |      |      |       |          |                            |  |

| FOREIGN PATENT DOCUMENTS |                 |      |         |       |          |             |    |
|--------------------------|-----------------|------|---------|-------|----------|-------------|----|
|                          | Document Number | Date | Country | Class | Subclass | Translation |    |
|                          |                 |      |         |       |          | Yes         | No |
|                          | AL              |      |         |       |          |             |    |
|                          | AM              |      |         |       |          |             |    |
|                          | AN              |      |         |       |          |             |    |
|                          | AO              |      |         |       |          |             |    |
|                          | AP              |      |         |       |          |             |    |

| OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) |  |  |  |
|---|--|--|--|
| AR  |  | <i>Flouting Body Effects</i> ; SOI DEVICE ELECTRICAL PROPERTIES: pp. 34-53 (pre Aug. 2001) |  |
| AS  |  |  |  |
| AT  |  |  |  |

|          |                 |
|----------|-----------------|
| EXAMINER | DATE CONSIDERED |
|----------|-----------------|

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

EV318280349

EV026160662US

MI22-1797

Dated: January, 2002

Micron Technology, Inc.

The stamp of the U.S. Patent and Trademark Office acknowledges receipt of the application for letters patent of the following:

Applicant: **Zhongze Wang**

Titled: **Silicon-On-Insulator Comprising Integrated Circuitry and Methods of Forming Silicon-On-Insulator Circuitry**

1. Return Postcard Receipt;
2. PTO Utility Application Transmittal Form (PTO/SB/05);
3. A \$1,898 check, and a \$40.00 check;
4. Fee Transmittal Form (PTO/SB/17) in duplicate;
5. 28 pages of Specification, Claims and Abstract plus title page;
6. Inventors Declaration newly executed original;
7. 3 sheets of formal drawings (Figs. 1-9);
8. Assignment of the invention to Micron Technology, Inc., and Recordation Cover Sheet;
9. Power of Attorney;
10. Information Disclosure Statement including PTO-1449 and cited references.

J1017 U.S. PTO

10/051981



01/16/02

**COPY**

**RECEIVED**

FEB 04 2002

WELLS ST. JOHN

Wells, St. John, Roberts,  
Gregory & Matkin, P.S.  
601 W. First, Suite 1300  
Spokane, WA 99201-3828



EV318280349